

DESCRIPTION

The GLF71307 is an ultra-efficiency, 2.0 A rated, integrated load switch with integrated slew rate control. The best in class efficiency makes it an ideal choice for use in IoT, mobile, and wearable electronics.

The GLF71307 features an ultra-efficient I_QSmart™ technology that supports the lowest quiescent current (I_Q) and shutdown current (I_{SD}) in the industry. Low I_Q and I_{SD} solutions help designers to reduce parasitic leakage current, improve system efficiency, and increase battery lifetime.

The GLF71307 integrated slew rate control greatly enhances system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF71307 can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

The GLF71307 Load Switch device is small utilizing a wafer level chip scale package with 4 bumps in a 0.77 mm x 0.77 mm x 0.46 mm die size and a 0.4mm bump pitch.

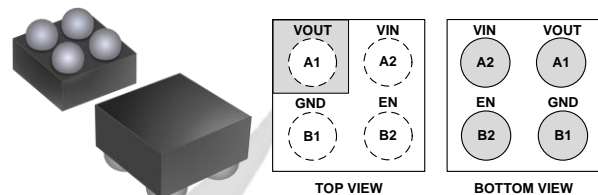
FEATURES

- Ultra-Low I_Q: 1 nA Typ @ 5.5 V_{IN}
- Ultra-Low I_{SD}: 19 nA Typ @ 5.5 V_{IN}
- Low R_{ON} = 34 mΩ Typ @ 5.5 V_{IN}
- I_{OUT} Max = 2.0 A
- Wide Input Range: 1.1 V to 5.5 V
6 V abs max
- Controlled Rise Time: 9 us at 3.3 V_{IN}
- Internal EN Pull-Down Resistor
- Integrated Output Discharge Switch
- Temperature Range: - 40 to 85 °C
- HBM: 6 kV, CDM: 2 kV
- Ultra-Small: 0.77 mm x 0.77 mm

APPLICATIONS

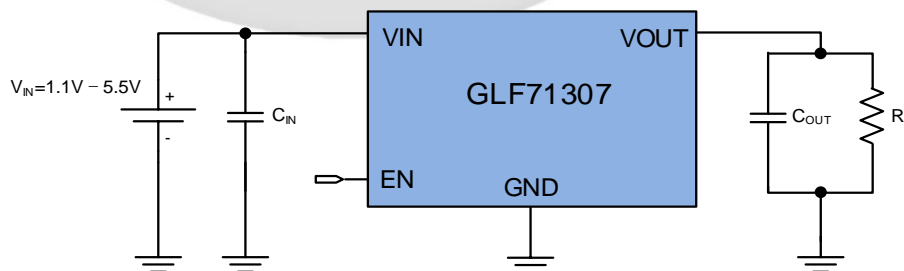
- Wearables
- Data Storage, SSD
- Mobile Devices
- Low Power Subsystems

PACKAGE



0.77 mm x 0.77 mm x 0.46 mm WLCSP

APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{ON} (Typ) at 5.5 V	Output Discharge	EN Activity	Availability
GLF71307	S	34 mΩ	85 Ω	High	Released

FUNCTIONAL BLOCK DIAGRAM

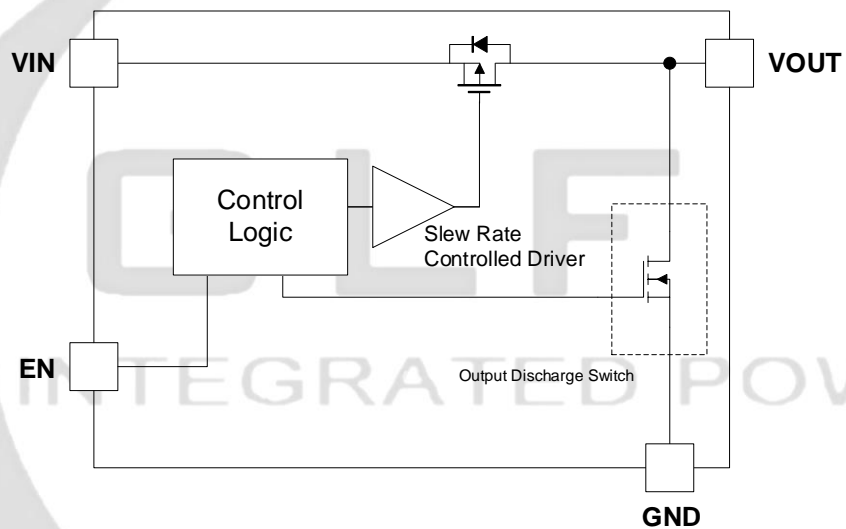
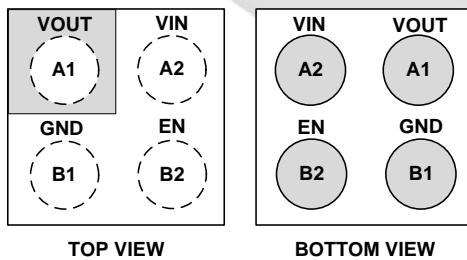


Figure 1. Functional Block Diagram

PIN CONFIGURATION

PIN DEFINITION



Pin #	Name	Description
A1	V _{OUT}	Switch Output
A2	V _{IN}	Switch Input. Supply Voltage for IC
B1	GND	Ground
B2	EN	Enable to control the switch

Figure 2. 0.77 mm x 0.77 mm x 0.46 mm WLCSP

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
V _{IN} , V _{OUT} , V _{EN}	Each Pin Voltage Range to GND	-0.3	6	V
I _{OUT}	Maximum Continuous Switch Current		2	A
P _D	Power Dissipation at T _A = 25 °C		1	W
T _{STG}	Storage Temperature	-65	150	°C
T _A	Operating Temperature Range	-40	85	°C
θ _{JA}	Thermal Resistance, Junction to Ambient (board dependent)		110	°C/W
ESD	Electrostatic Discharge Capability	Human Body Model, JESD22-A114	6	kV
		Charged Device Model, JESD22-C101	2	

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
V _{IN}	Supply Voltage	1.1	5.5	V
T _A	Ambient Operating Temperature	-40	+85	°C

ELECTRICAL CHARACTERISTICS

 Values are at $V_{IN} = 3.3\text{ V}$ and $T_A = 25\text{ °C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
Basic Operation							
V_{IN}	Supply Voltage		1.1		5.5	V	
I_Q	Quiescent Current	EN = Enable, $I_{OUT}=0\text{ mA}$, $V_{IN} = V_{EN}=5.5\text{ V}$		1		nA	
		EN=Enable, $I_{OUT}=0\text{ mA}$, $V_{IN}=V_{EN}=5.5\text{ V}$, $T_a=85\text{ °C}$ ⁽⁴⁾		7			
I_{SD}	Shutdown Current	EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=1.1\text{ V}$		3		nA	
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=1.8\text{ V}$		4			
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=3.3\text{ V}$		6			
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=4.5\text{ V}$		9			
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=5.5\text{ V}$		19	50		
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=5.5\text{ V}$, $T_a=55\text{ °C}$ ⁽⁴⁾		110			
		EN = Disable, $I_{OUT}=0\text{ mA}$, $V_{IN}=5.5\text{ V}$, $T_a=85\text{ °C}$ ⁽⁴⁾		600			
R_{ON}	On-Resistance	$V_{IN}=5.5\text{ V}$, $I_{OUT}= 500\text{ mA}$	$T_a=25\text{ °C}$		34	47	mΩ
			$T_a=85\text{ °C}$ ⁽⁴⁾		40		
		$V_{IN}=3.3\text{ V}$, $I_{OUT}= 500\text{ mA}$	$T_a=25\text{ °C}$		42	56	
			$T_a=85\text{ °C}$ ⁽⁴⁾		50		
		$V_{IN}=1.8\text{ V}$, $I_{OUT}= 300\text{ mA}$	$T_a=25\text{ °C}$		68		
		$V_{IN}=1.1\text{ V}$, $I_{OUT}= 100\text{ mA}$	$T_a=25\text{ °C}$		125		
R_{DSC}	Output Discharge Resistance	EN=Low , $I_{FORCE}= 10\text{ mA}$	70	85	100	Ω	
V_{IH}	EN Input Logic High Voltage	$V_{IN}=1.1\text{ V} - 1.8\text{ V}$	0.9			V	
		$V_{IN}=1.8\text{ V} - 5.5\text{ V}$	1.2			V	
V_{IL}	EN Input Logic Low Voltage	$V_{IN}=1.1\text{ V} - 1.8\text{ V}$			0.3	V	
		$V_{IN}=1.8\text{ V} - 5.5\text{ V}$			0.4	V	
R_{EN}	EN Pulldown resistance	Internal Resistance	7	10.1	13	MΩ	
I_{EN}	EN Current	$E_N=5.5\text{ V}$			0.8	μA	
Switching Characteristics							
t_{dON}	Turn-On Delay ⁽¹⁾	$R_L=150\text{ Ω}$, $C_{OUT}=0.1\text{ μF}$		7.4		μs	
t_R	V_{OUT} Rise Time ⁽¹⁾			8.7			
t_{dON}	Turn-On Delay ^(1,4)	$R_L=500\text{ Ω}$, $C_{OUT}=0.1\text{ μF}$		7.3			
t_R	V_{OUT} Rise Time ^(1,4)			8.2			
t_{dOFF}	Turn-Off Delay ^(2,3,4)	$R_L=10\text{ Ω}$, $C_{OUT}=0.1\text{ μF}$		0.5			
t_F	V_{OUT} Fall Time ^(2,3,4)			1.0			
t_{dOFF}	Turn-Off Delay ^(2,3,4)	$R_L=500\text{ Ω}$, $C_{OUT}=0.1\text{ μF}$		1.1			
t_F	V_{OUT} Fall Time ^(2,3,4)			20.6			

- Notes:
- $t_{ON} = t_{dON} + t_R$
 - $t_{OFF} = t_{dOFF} + t_F$
 - Output discharge path is enabled during off.
 - By design; characterized; not production tested.

TIMING DIAGRAM

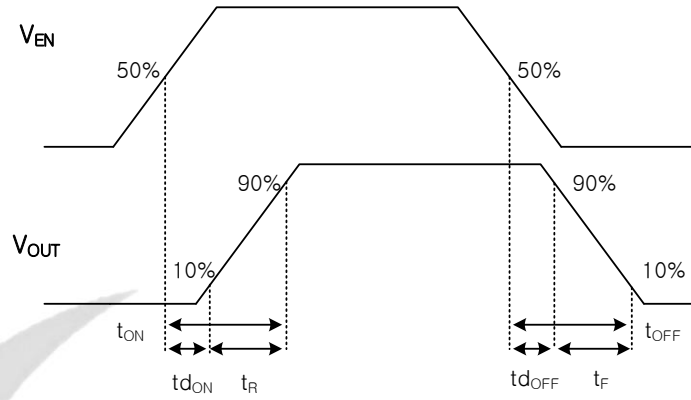


Figure 3. Timing Diagram



TYPICAL PERFORMANCE CHARACTERISTICS

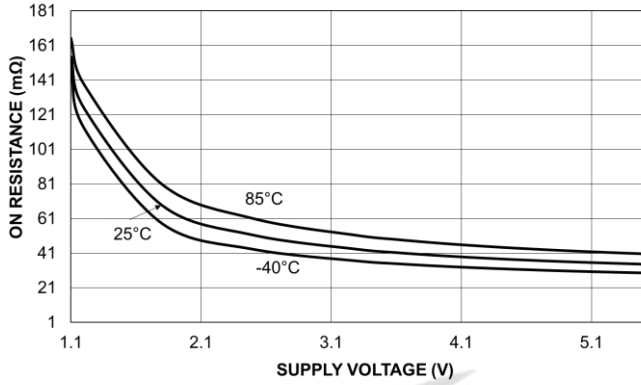


Figure 4. On-Resistance vs. Supply Voltage

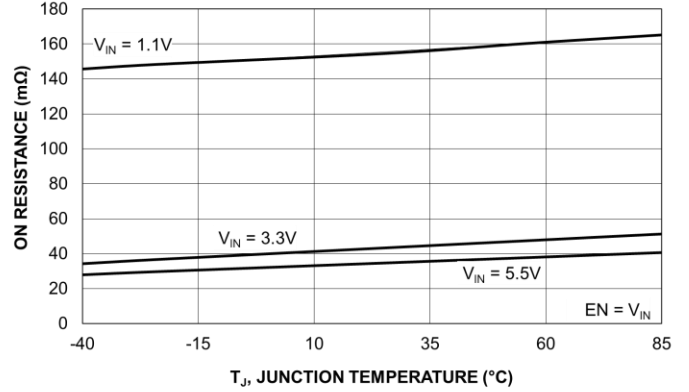


Figure 5. On-Resistance vs. Temperature

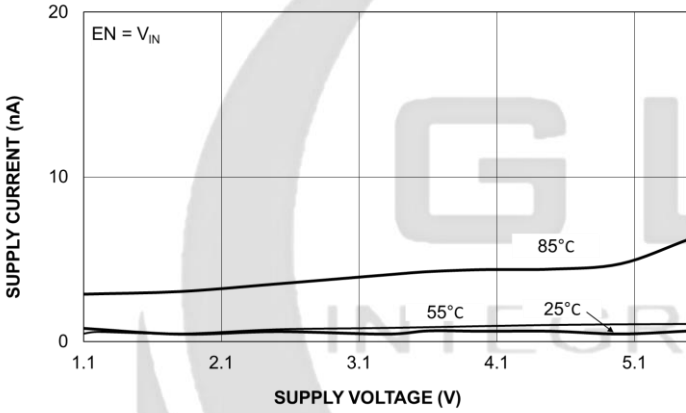


Figure 6. Quiescent Current vs. Supply Voltage

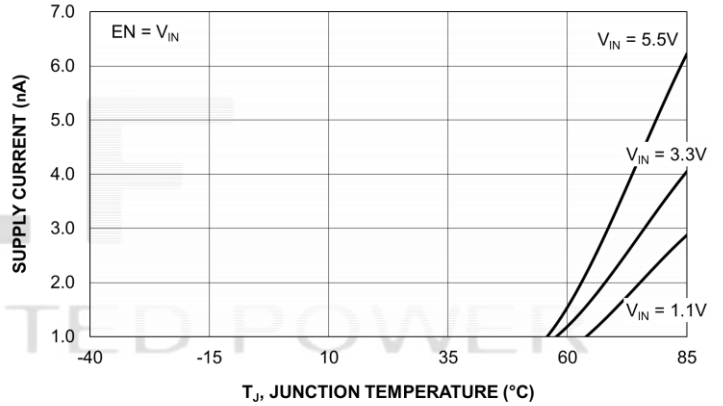


Figure 7. Quiescent Current vs. Temperature

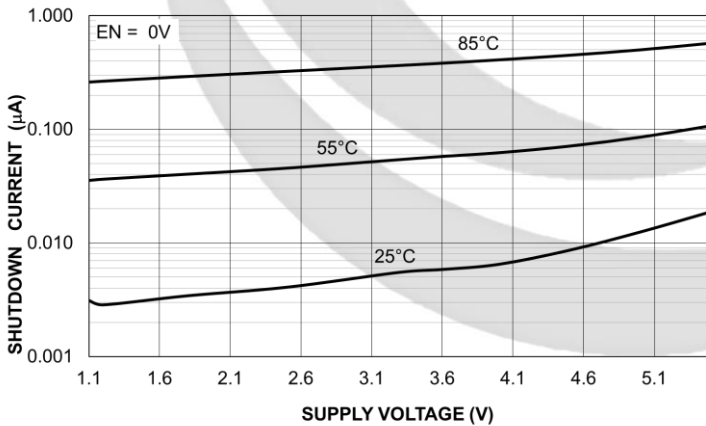


Figure 8. Shutdown Current vs. Supply Voltage

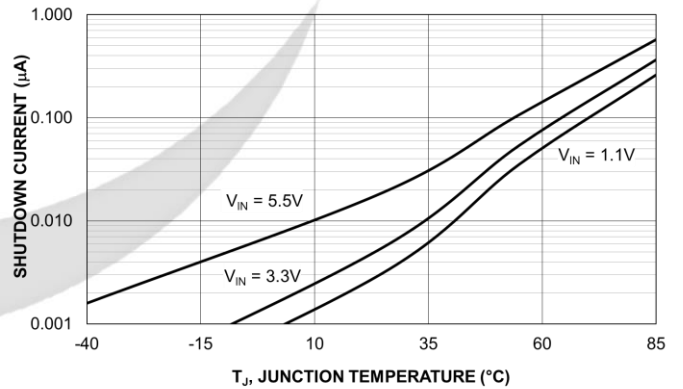


Figure 9. Shutdown Current vs. Temperature

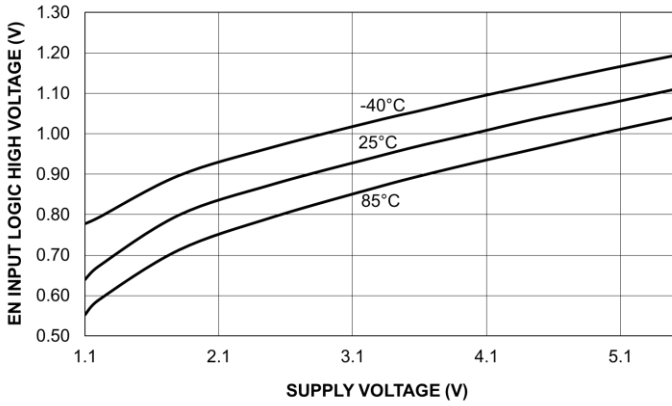


Figure 10. EN Input Logic High Threshold

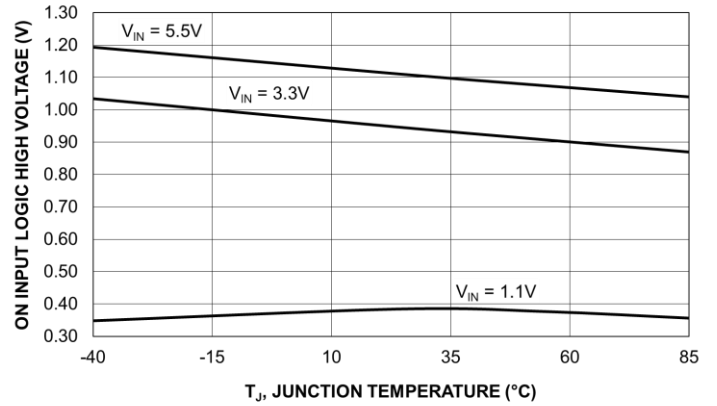


Figure 11. EN Input Logic High Threshold Vs. Temperature

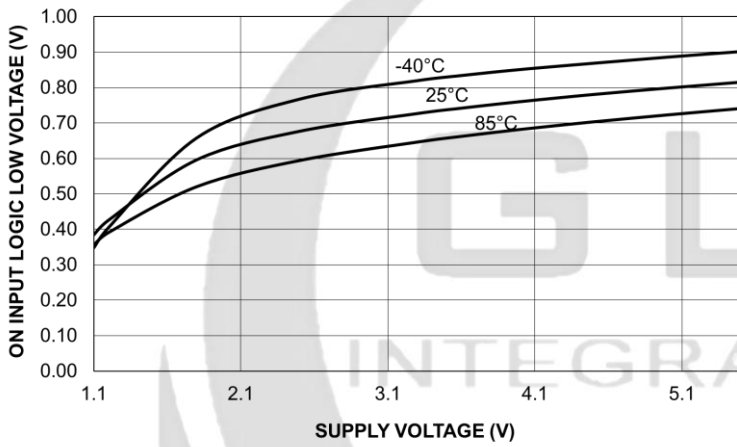


Figure 12. EN Input Logic Low Threshold

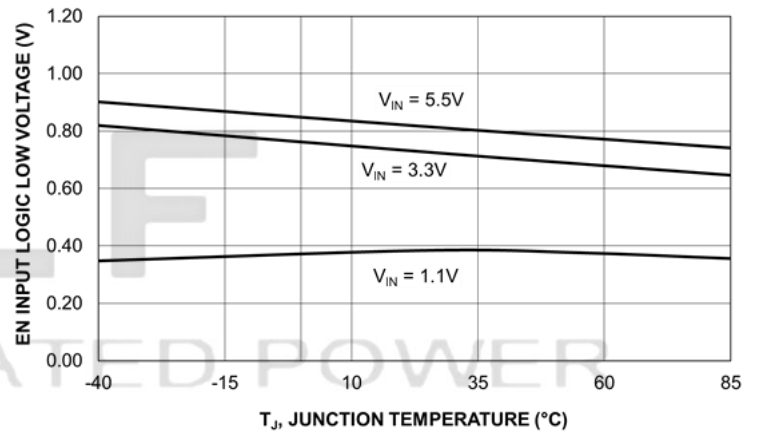


Figure 13. EN Input Logic Low Threshold Vs. Temperature

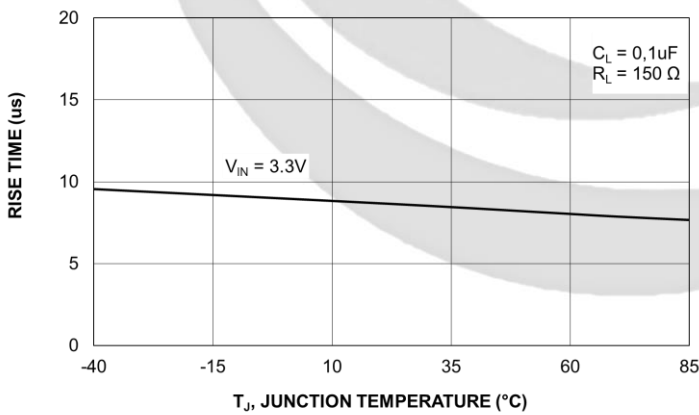


Figure 14. V_{OUT} Rise Time vs. Temperature

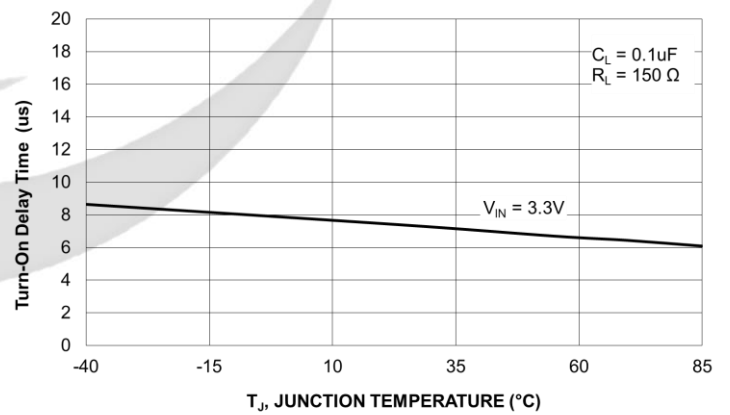


Figure 15. Turn-On Delay Time vs. Temperature

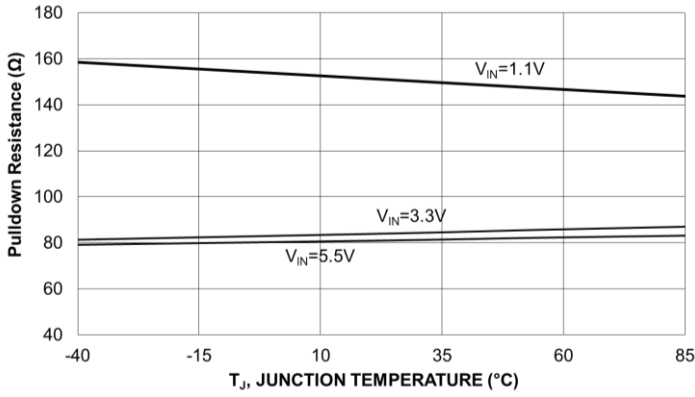


Figure 16. Pulldown Resistance vs. Temperature

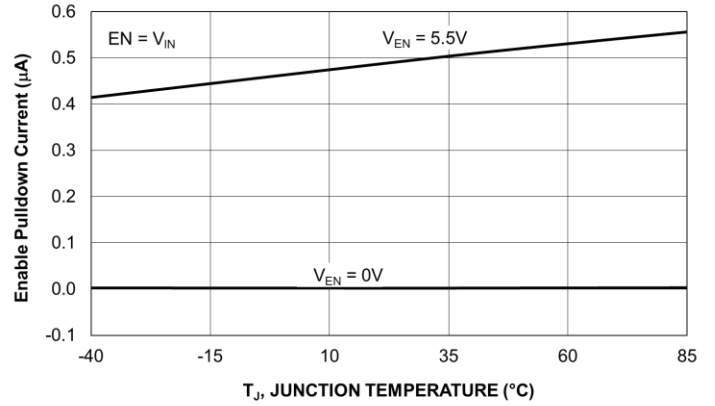


Figure 17. Enable Pulldown Current vs. Temperature

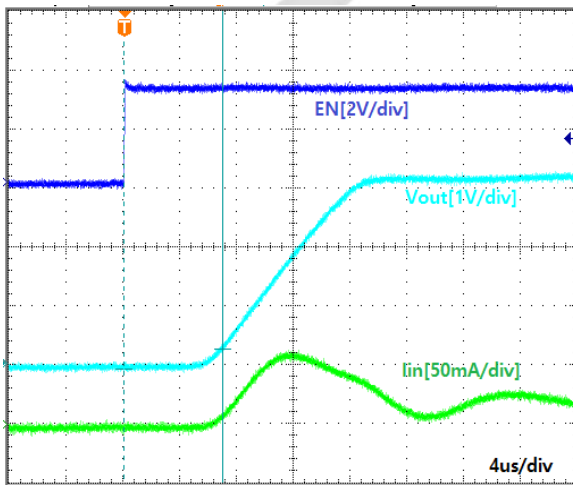


Figure 18. Turn-On Response
 $V_{IN}=3.3\text{ V}$, $C_{IN}=1.0\text{ uF}$, $C_{OUT}=0.1\text{ uF}$, $R_L=150\text{ }\Omega$

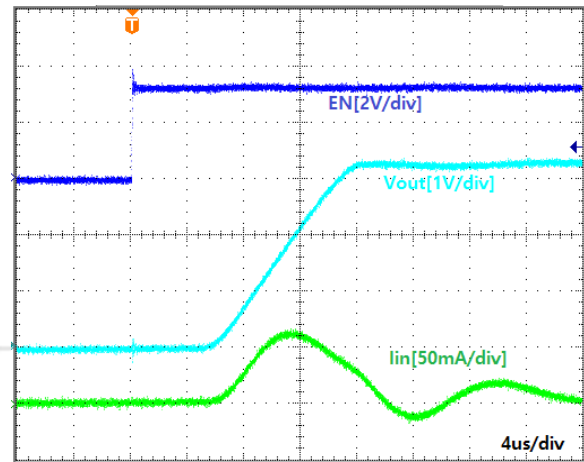


Figure 19. Turn-On Response
 $V_{IN}=3.3\text{ V}$, $C_{IN}=1.0\text{ uF}$, $C_{OUT}=0.1\text{ uF}$, $R_L=500\text{ }\Omega$

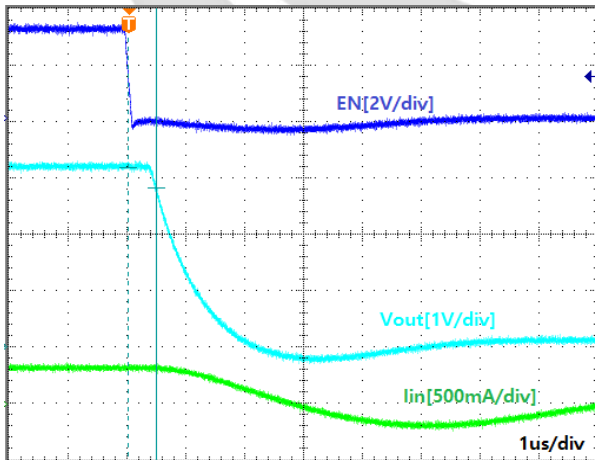


Figure 20. Turn-Off Response, Output Discharge
 $V_{IN}=3.3\text{ V}$, $C_{IN}=1.0\text{ uF}$, $C_{OUT}=0.1\text{ uF}$, $R_L=10\text{ }\Omega$

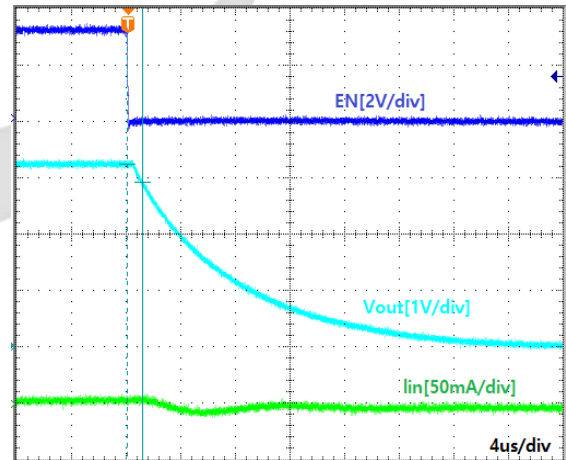


Figure 21. Turn-Off Response, Output Discharge
 $V_{IN}=3.3\text{ V}$, $C_{IN}=1.0\text{ uF}$, $C_{OUT}=0.1\text{ uF}$, $R_L=500\text{ }\Omega$

APPLICATION INFORMATION

The GLF71307 is an integrated 2.0 A, Ultra-Efficient I_QSmart™ LoadSwitch device with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 1.1 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power. The package is a 0.77 mm x 0.77 mm x 0.5 mm wafer level chip scale package, saving space in compact applications. It is constructed using 4 bumps, with a 0.4 mm pitch for manufacturability.

Input Capacitor

A capacitor is recommended to be placed close to the V_{IN} pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

An output capacitor is recommended to mitigate voltage undershoot on the output pin the moment when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be placed close to the V_{OUT} and GND pins.

EN pin

The GLF71307 can be activated by EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known “off state” when no EN signal is applied from an external controller.

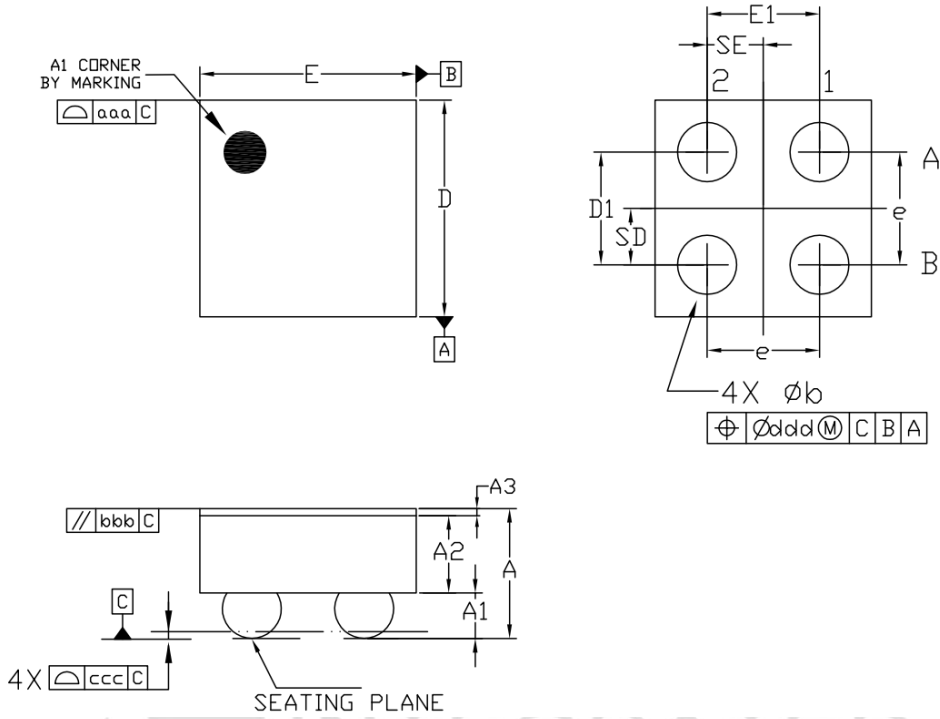
Output Discharge Function

The GLF71307 has an internal discharge N-channel FET switch on the V_{OUT} pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

Board Layout

All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for V_{IN}, V_{OUT}, and GND will help reduce voltage drops, and parasitic effects during dynamic operation as well as improve the thermal performance at high load currents.

PACKAGE OUTLINE



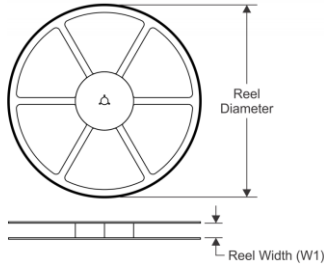
Dimensional Ref.			
REF.	Min.	Nom.	Max.
A	0.410	0.460	0.510
A1	0.135	0.160	0.185
A2	0.250	0.275	0.300
A3	0.020	0.025	0.030
D	0.755	0.770	0.785
E	0.755	0.770	0.785
D1	0.350	0.400	0.450
E1	0.350	0.400	0.450
b	0.170	0.210	0.250
e	0.400 BSC		
SD	0.200 BSC		
SE	0.200 BSC		
Tol. of Form&Position			
aaa	0.10		
bbb	0.10		
ccc	0.05		
ddd	0.05		

Notes

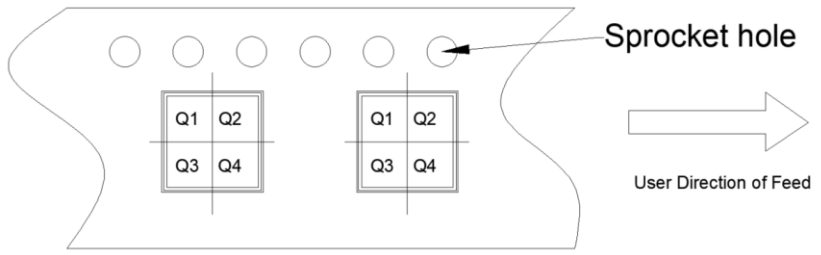
1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES)
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
3. A3: BACKSIDE LAMINATION

TAPE AND REEL INFORMATION

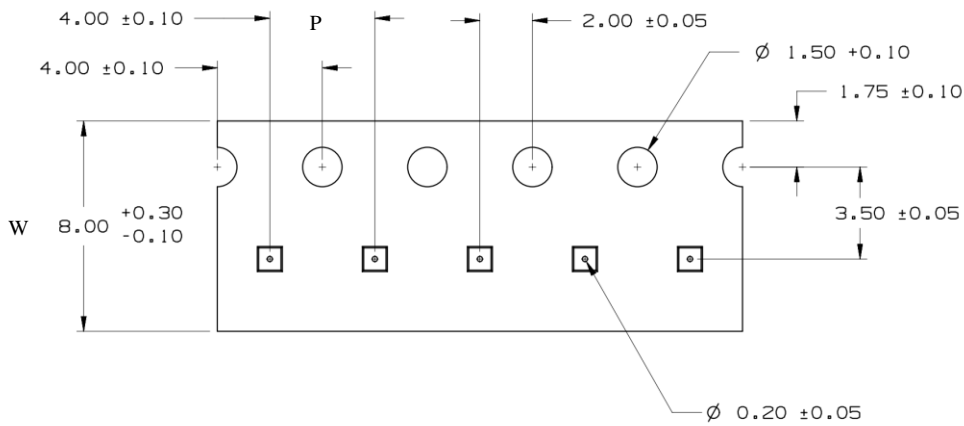
REEL DIMENSIONS



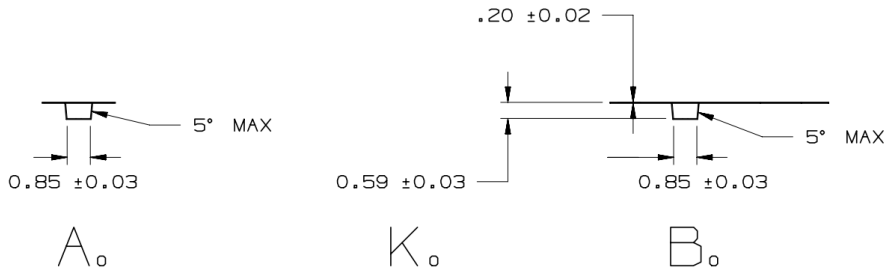
QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE



TAPE DIMENSIONS



POWER



Device	Package	Pins	SPQ	Reel Diameter(mm)	Reel Width W1	A0	B0	K0	P	W	Pin1
GLF71307	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P: Pitch between successive cavity centers

SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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